

Please complete and return along with your other supporting exhibits.

Please state what Type of Emission(s) your device(s) has. Refer to FCC part 2.201 and 2.202 for more information.

Please state what frequency range(s) your device(s) operates over. Please provide "From" and "To" frequencies.

Please state the range(s) your device(s) operates over, and how the power adjustment is controlled.

[illegible]

SECTION D Maximum Power Rating

Please specify the maximum power rating(s) of your device(s) as defined in the applicable part(s) of the FCC rules.

[illegible]

SECTION E DC Voltages

Please specify the DC voltages applied to the DC currents into the several elements of the final radio frequency amplifying device for normal operation over the power range.

[illegible]

SECTION F Tune Up Procedure

Please provide Information about your Tune Up Procedure over the power range (previously specified) or at the specific power levels (also specified). For equipment employing digital modulation techniques, a detailed description of the modulation system to be employed must be provided. This will at least include the response characteristics (Frequency, Phase and Amplitude) or any filters provided, and a description of the modulation wave train, this shall be submitted for the maximum rated conditions under which the equipment will be operated.

See details in document below

Panasonic

Panasonic Mobile Communications Development of Europe Limited

Supplement to FCC Form A.

Model: EB-X800

FCC ID: NWJ21C001A

Function of the Active Devices-- Pursuant 2.983 (d6)

Transmitter

U501	PMB2258	GSM Limiter Amplifier IC
U503	RF3146TR13	Tri Band PA Module

Receiver

U500	PMB6258	GSM Transceiver IC
U502	GN06006L01MC	Antenna Switch Module

Synthesizer

Y500	MAA3260A	Voltage Controlled Temperature Compensated Crystal Oscillator
------	----------	---

Power control

U300	AN32061A	Regulator/Audio IC
U304	PMB6811	Regulator IC
Q300	MCH3411-TL-E	Switching Transistor
Q301	SI3443DV-T1	Switching Transistor
U100	PMB8870	Base Band IC
U200	OMAP310GZZGR	Application IC

Circuit Descriptions

A. Means for Stabilizing Transmitter Output Frequency

To meet requirements of Subpart J Section 2.983(d10)

As a result of the following approach, the frequency stabilization requirement is achieved

1. Phase Locking

A Voltage Controlled local Oscillator (VCO) whose frequency output is divided in half to produce the desired RF frequency produces the transmitter carrier. The oscillator is phase locked to a reference oscillator by an independent PLL (Phased Locked Loop) circuit. The reference oscillator is a Voltage Controlled Temperature Compensated Crystal Oscillator (VCTCXO). Therefore, the transmitter carrier frequency has the same stability as the VCTCXO.

2. VCTCXO

The output frequency of the VCTCXO is frequency locked to the RF signal transmitted from a cellular base station by means of an Automatic Frequency Control (AFC) circuit. The received reference signal from the base station is down converted and compared to the mobile station internal frequency. Any differences between the base station reference frequency and the mobile station internal frequency are corrected by fine tuning the VCTCXO frequency. The AFC control circuit is designed such that the transmitter carrier output is maintained within $\pm 0.1\text{ppm}$ of the base station reference frequency.

B. Means for Suppressing Spurious Radiation

To meet requirements of Subpart J Section 2.983(d-11)

As a result of the following approach, the attenuation requirement for spurious and harmonic radiation is achieved.

1. Shielding

The RF and Digital sections are enclosed by 3 shield can enclosures. These enclosures are soldered on the gold plated ground of the PCB. All oscillators are enclosed.

2. Filtering

Filtering is provided at multiple points in the transmitter chain. Between the modulator and limiter amplifier IC, integrated low pass filters are included to reduce TX harmonics. For 900MHz operation the transmit signal is filtered with a SAW TXBPF (Surface Acoustical Wave Transmit Band Pass Filter) prior to final amplification by the PA Module. Following amplification by the PA module additional low pass filtering is provided in the ASM (Antenna Switch Module). The low pass filters contained in the ASM are separated by band. One filter is provided for 900MHz operation and a separate filter is provided for 1800 & 1900 MHz operation.

C. Means for limiting Transmitter Output Power

To meet requirements of Subpart J Section 2.983(d-11)

The PA module employed in the design contains an integrated power control function. This power control method is based on control of collector voltage. A high-speed control loop is incorporated to regulate the collector voltage of the amplifier while maintaining a constant bias on each of the gain stages. By regulating collector voltage, the amplification stages are held in saturation across all power levels. As a result, output power fluctuations associated with variation in the supply voltage, input power, and temperature are minimized. A control voltage provided by the base band IC interfacing the PA module is used to select the desired output power of the transmitter.

D. Means for Digital Modulation

To meet requirements of Subpart J Section 2.983(d-11)

The GSM Transceiver IC employed in the design supports a direct quadrature modulation system. That is, I & Q signals provided from the base band IC are directly up-converted to RF by this modulator. To limit the bandwidth of the transmitted signal, 0.3 Gaussian pre-modulation filtering is applied to the I & Q signals prior to modulating the carrier. The Gaussian pre-filtering is performed within the base band IC. In addition, low pass filtering contained in the Transceiver IC, is used to remove any additional digital clock noise. The modulation data rate for the signal is 270.833Kbps.